

2SA633

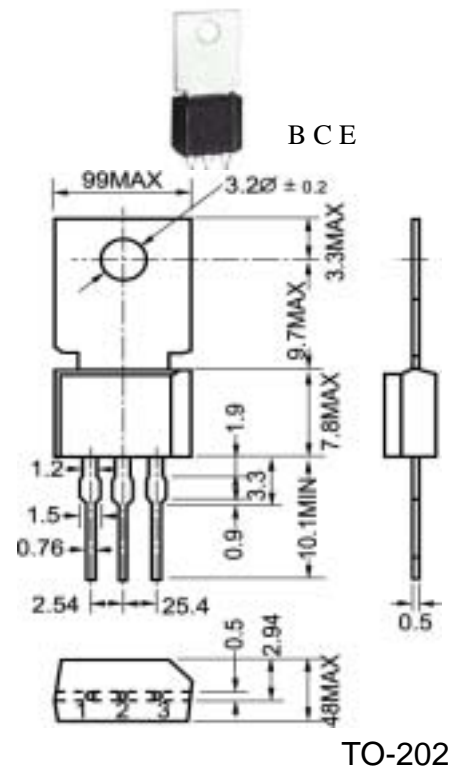
Silicon PNP Transistors

◆ Features

. With TO-202 package

◆ Absolute Maximum Ratings $T_c=25^\circ\text{C}$

SYMBOL	PARAMETER	RATING	UNIT
V_{CB0}	Collector to base voltage	30	V
V_{CEO}	Collector to emitter voltage	30	V
V_{EBO}	Emitter to base voltage	5.0	V
I_B	Base collector current		A
I_C	Collector current	2.0	A
P_C	Collector power dissipation	10	W
T_j	Junction temperature	150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55~+150	$^\circ\text{C}$



◆ Electrical Characteristics $T_c=25^\circ\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I_{CBO}	Collector-base cut-off current	$V_{CB}=30\text{V}; I_E=0$			100	μA
I_{EBO}	Emitter-base cut-off current	$V_{EB}=5.0\text{V}; I_C=0$			100	μA
I_{CEO}	Collector-emitter cut-off current	$V_{CE}=30\text{V}; I_B=0$			0.5	mA
V_{CB0}	Collector-base breakdown voltage					
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=20\text{mA}; I_B=0$	30			V
V_{EBO}	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	5			
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	$I_C=1.5\text{A}; I_B=0.15\text{A}$			1.0	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio	$I_C=1\text{A}; V_{CE}=5\text{V}$	80			
h_{FE-2}	Forward current transfer ratio					
h_{FE-3}	Forward current transfer ratio					